

Features

- · Split Gate Trench MOSFET Technology
- · Excellent Package for Heat Dissipation
- High Density Cell Design for Low RDS(ON)
- Halogen Free. "Green" Device (Note 1)
- · Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)
- Moisture Sensitivity Level 1

Maximum Ratings

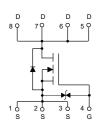
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 20°C/W Junction to Ambient(t≤10s)⁽²⁾
- Thermal Resistance: 50°C/W Junction to Ambient(Steady-State)⁽²⁾
- Thermal Resistance: 2.1°C/W Junction to Case(Steady-State)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Volltage	V _{GS}	±20	V
Continuous Drain Current	I _D	38	Α
Pulsed Drain Current ⁽³⁾	I _{DM}	160	Α
Total Power Dissipation ⁽⁴⁾	P _D	60	W
Single Pulsed Avalanche Energy ⁽⁵⁾	E _{AS}	81	mJ

Note:

- 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 2. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The Power dissipation P_{DSM} is based on R_{θJA} t≤ 10s and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.
- 3. Repetitive rating; pulse width limited by max. junction temperature.
- 4. P_D is based on max. junction temperature, using junction-case thermal resistance.
- 5. $T_J = 25$ °C, $V_{DD} = 50$ V, $R_G = 25\Omega$, L=0.5mH.

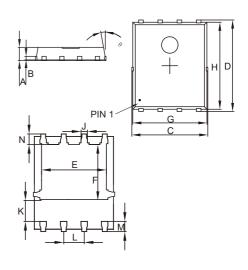
Internal Structure and Marking Code





N-CHANNEL MOSFET

DFN5060



	DIMENSIONS					
DIM	INCHES		MM		NOTE	
	MIN	MAX	MIN	MAX	INOIL	
Α	0.031	0.047	0.80	1.20		
В	0.010		0.254		TYP.	
С	0.193	0.222	4.90	5.64		
D	0.232	0.250	5.90	6.35		
Е	0.148	0.167	3.75	4.25		
F	0.126	0.154	3.20	3.92		
G	0.189	0.213	4.80	5.40		
Н	0.222	0.239	5.65	6.06		
K	0.045	0.059	1.15	1.50		
J	0.012	0.020	0.30	0.50		
L	0.046	0.054	1.17	1.37		
M	0.012	0.028	0.30	0.71		
N	0.016	0.028	0.40	0.71		

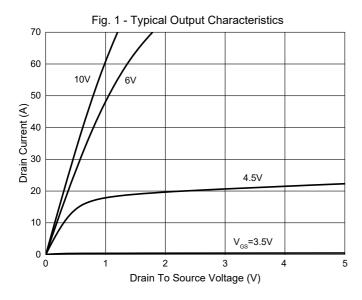


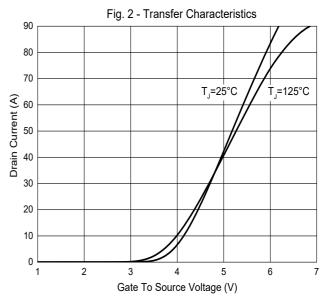
Electrical Characteristics @ 25°C (Unless Otherwise Specified)

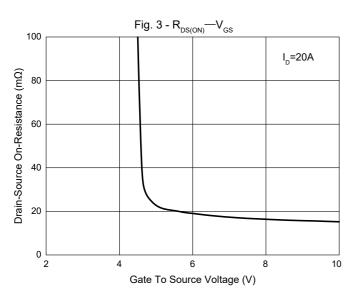
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static Characteristics	<u> </u>		1	1		ı	
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250μA	100			V	
Gate-Source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	μA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V			0.3	μA	
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	2	2.8	4	V	
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =20A		15.5	20	mΩ	
Gate Resistance	R_{G}	f=1MHz, Open drain		1		Ω	
Diode Characteristics				1	-		
Continuous Body Diode Current	Is				38	Α	
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =20A		0.8	1.3	V	
Reverse Recovery Time	t _{rr}	1 -20A dl /dt-400A/		41.2		ns	
Reverse Recovery Charge	Q _{rr}	l _F =20A, dl _F /dt=100A/μs		39.7		nC	
Dynamic Characteristics			·				
Input Capacitance	C _{iss}			1209			
Output Capacitance	C _{oss}	V _{DS} =50V,V _{GS} =0V,f=1MHz		405		pF	
Reverse Transfer Capacitance	C _{rss}			23.5			
Total Gate Charge	Q_g			17.5			
Gate-Source Charge	Q _{gs}	V _{DS} =50V,V _{GS} =10V,I _D =25A		7.4		nC	
Gate-Drain Charge	Q_{gd}			2.0			
Turn-On Delay Time	t _{d(on)}			11.4			
Turn-On Rise Time	t _r	V _{DS} =50V, V _{GEN} =10V,		55.3		no	
Turn-Off Delay Time	t _{d(off)}	$R_G=2.2\Omega$, $I_{DS}=25A$		15.2		ns	
Turn-Off Fall Time	t _f			58.4			

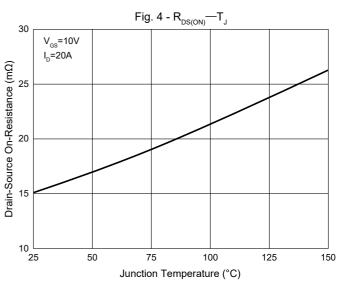


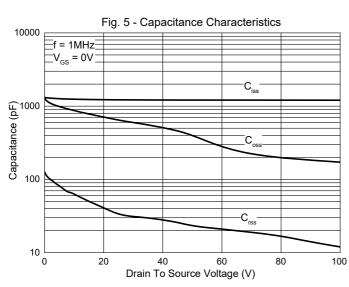
Curve Characteristics

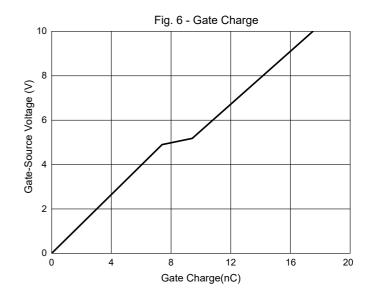






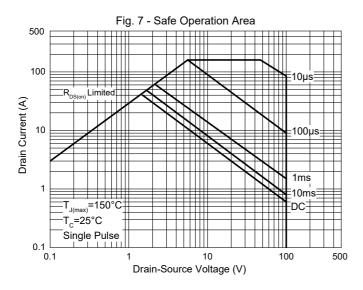


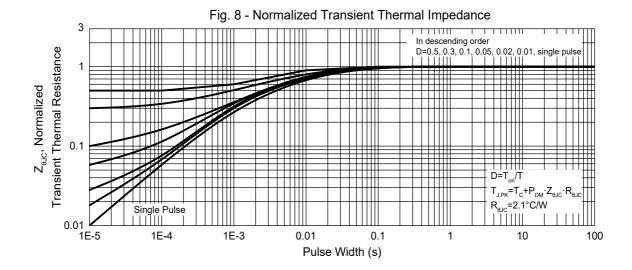






Curve Characteristics





Rev.3-2-04092022 4/5 MCCSEMI.COM



Ordering Information

Device	Packing	
Part Number-TP	Tape&Reel: 5Kpcs/Reel	

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